Micro Commercial Components
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2SD716

NPN Silicon Power Transistors

Features

- Power amplifier applications
- Complementary to 2SB686
- Recommended for 30~30W high-fidelity frequency amplifier output stage

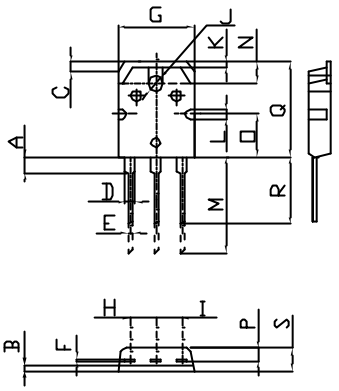
Maximum Ratings

Symbol	Rating	Rating	Unit
V_{CEO}	Collector-Emitter Voltage	100	V
V_{CBO}	Collector-Base Voltage	100	V
V_{EBO}	Emitter-Base Voltage	5.0	V
I_C	Collector Current	6.0	A
P_C	Collector power dissipation	60	W
T_J	Junction Temperature	-55 to +150	^{O}C
T_{STG}	Storage Temperature	-55 to +150	^{O}C

Electrical Characteristics @ 25^{O}C Unless Otherwise Specified

Symbol	Parameter	Min	Max	Units
OFF CHARACTERISTICS				
$V_{(BR)CEO}$	Collector-Emitter Breakdown Voltage (I_C=50mAdc, I_B=0)	100	---	Vdc
I_{CBO}	Collector-Base Cutoff Current (V_{CB}=100Vdc,I_E=0)	---	10	uAdc
I_{EBO}	Emitter-Base Cutoff Current (V_{EB}=5.0Vdc, I_C=0)	---	10	uAdc
ON CHARACTERISTICS				
h_{FE}	Forward Current Transfer ratio (I_C=1.0Adc, V_{CE}=5.0Vdc)	55	160	---
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage (I_C=4.0Adc, I_B=0.4Adc)	---	2.0	Vdc
$V_{BE(SAT)}$	Base-Emitter Saturation Voltage (I_C=4.0Adc,V_{CE}=5.0Vdc)	---	1.5	Vdc

TO-3P(I)



DIMENSIONS					
	INCHES		MM		
DIM	MIN	MAX	MIN	MAX	NOTE
A	---	.130	---	3.30	
B	---	.071	---	1.80	
C	.079		2.00		
D	.067	.091	1.70	2.30	
E	.030	.051	.75	1.30	
F	.012	.028	.30	.70	
G	---	.626	---	15.90	
H	.205	.220	5.20	5.60	
I	.207	.222	5.25	5.65	
J	.118	.134	3.00	3.40	∅
K	.039		1.00		
L	.079		2.00		
M	.748	.827	19.00	21.00	
N	.177		4.50		
O	.354		9.00		
P	.110		2.80		
Q	.067	.091	1.70	2.30	
R	.512	.551	13.00	14.00	
S	---	.189	---	4.80	